NSN 5961-01-245-3669

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Unitized Semiconductor Devices - Page 1 of 1



View Online at https://aerobasegroup.com/nsn/5961-01-245-3669 **Inclosure Material:** Ceramic **Overall Length:** 0.785 inches **Overall Height:** 0.200 inches **Overall Width:** 0.325 inches Joint Electronic Device Engineering Council/jedec/case Outline Designation: To-116 **Component Name And Quantity:** 4 transistor **Mounting Method:** Press fit **Features Provided:** Electrostatic sensitive and hermetically sealed case **Semiconductor Material:** Silicon all transistor Voltage Rating In Volts Per Characteristic: -40.0 collector to emitter voltage, dc all transistor and -40.0 collector to base voltage, dc all transistor and -5.0 emitter to base voltage, dc all transistor **Current Rating Per Characteristic:** -1.00 amperes source cutoff current all transistor **Power Rating Per Characteristic:** 6.3 watts small-signal input power, common-collector absolute all transistor **Transfer Ratio:** 20.0 static forward current transfer ratio, common-emitter all transistor **Maximum Operating Tempurature Per Measurement Point:** 200.0 degrees celsius ambient air **Special Features:** All transistor junction pattern arrangement: pnp **Terminal Type And Quantity:** 14 uninsulated wire lead Shelf Life: N/a **Unit Of Measure: Demilitarization:** No